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U.S. PATENT DOCUMENTS

INDEX TITLE	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA		5,906,680	5/25/1999	Meyerson			
AB		6,190,375	2/2001	Kubo et al.			
AD		5,693,934	11/1997	Candelaria et al.			
AF		6,306,211	10/2001	Takabashi et al.			

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INDEX TITLE	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AC		2002/0160605	10/2002	Kanzawa et al.			
AE		2002/0016085	2/2002	Huang et al.			

FOREIGN PATENT DOCUMENTS

INDEX TITLE	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AG	E. Kasper et al. "Growth of 1D Gax SiGe-Heteroepitaxial Transistor (HBT) Structures," Jpn. J. Appl. Phys., Vol. 33 Pt. 1, No. 4B, April 1994, pp2412-2418;
AH	H.L. Oaten et al. in the paper entitled "Carbon Doped SiGe Heterojunction Bipolar Transistors for High Frequency Application," IEEE BCTM 7.1, 1999 pp. 109-116.

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DATE CONSIDERED

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